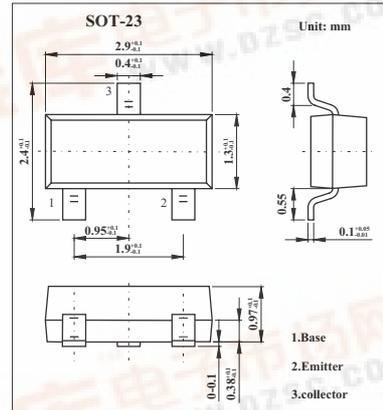


SMD Type Transistors

NPN Switching Transistor  
BSV52

■ Features

- High current (max. 100 mA).
- Low voltage (max. 12 V).



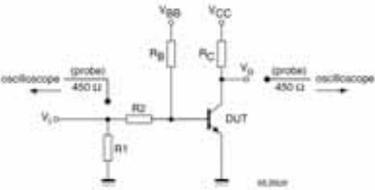
■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	20	V
Collector-emitter voltage	V <sub>CE0</sub>	12	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Collector current	I <sub>C</sub>	100	mA
Peak collector current	I <sub>CM</sub>	200	mA
Peak base current	I <sub>BM</sub>	100	mA
Total power dissipation	P <sub>tot</sub>	250	mW
Storage temperature	T <sub>stg</sub>	-65 to +150	°C
Junction temperature	T <sub>j</sub>	150	°C
Operating ambient temperature	R <sub>amb</sub>	-65 to +150	°C
Thermal resistance from junction to ambient *	R <sub>th j-a</sub>	500	K/W

\* Transistor mounted on an FR4 printed-circuit board.

## BSV52

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit	
Collector cutoff current	$I_{CBO}$	$I_E = 0; V_{CB} = 20\text{ V}$			400	nA	
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 125^\circ\text{C}$			30	$\mu\text{A}$	
Emitter cutoff current	$I_{EBO}$	$I_C = 0; V_{EB} = 4\text{ V}$			100	nA	
DC current gain	$h_{FE}$	$V_{CE} = 1\text{ V}; I_C = 10\text{ mA}$	40		120		
collector-emitter saturation voltage	$V_{CEsat}$	$I_C = 10\text{ mA}; I_B = 300\text{ }\mu\text{A}$			300	mV	
		$I_C = 10\text{ mA}; I_B = 1\text{ mA}$			250	mV	
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$			400	mV	
base-emitter saturation voltage	$V_{BEsat}$	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	700		850	mV	
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$			1.4	V	
Collector capacitance	$C_c$	$I_E = i_E = 0; V_{CB} = 5\text{ V}; f = 1\text{ MHz}$			4	pF	
Emitter capacitance	$C_e$	$I_C = i_C = 0; V_{EB} = 1\text{ V}; f = 1\text{ MHz}$			4.5	pF	
Transition frequency	$f_T$	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	400	500		MHz	
Turn-on time	$t_{on}$	$I_{Con} = 10\text{ mA}; I_{Bon} = 3\text{ mA}; I_{Boff} = -1.5\text{ mA}$			10	ns	
Delay time	$t_d$				4	ns	
Rise time	$t_r$					6	ns
Turn-off time	$t_{off}$					20	ns
Storage time	$t_s$		$V_1 = 0.5\text{ V to }4.2\text{ V}; T = 500\text{ }\mu\text{s}; t_p = 10\text{ }\mu\text{s}; t_f = t_r \leq 3\text{ ns}; R_1 = 56\text{ }\Omega; R_2 = 1\text{ k}\Omega; R_B = 1\text{ k}\Omega; R_C = 270\text{ }\Omega;$			10	ns
Fall time	$t_f$		$V_{BB} = 0.2\text{ V}; V_{CC} = 2.7\text{ V};$ Oscilloscope: input impedance $Z_i = 50\text{ }\Omega;$			10	ns

## ■ Marking

Marking	B2
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